

PNP/PNP matched double transistor

5 July 2023

**Product data sheet** 

#### 1. General description

PNP/PNP matched double transistor in a small SOT457 (SC-74) Surface-Mounted Device (SMD) plastic package. The transistors are fully isolated internally.

#### 2. Features and benefits

- Current gain matching
- Base-emitter voltage matching
- Drop-in replacement for standard double transistors
- AEC-Q101 qualified

#### 3. Applications

- Current mirror
- Differential amplifier

#### 4. Quick reference data

| Symbol                             | Parameter                     | Conditions  |     | Min | Тур | Max  | Unit |
|------------------------------------|-------------------------------|---|-----|-----|-----|------|------|
| Oymbol                             | I didilletei                  | Conditions  |     |     | тур | Max  | Unit |
| Per transist                       | or                            |   |     |     |     |      |      |
| V <sub>CEO</sub>                   | collector-emitter<br>voltage  | open base   |     | -   | -   | -45  | V    |
| I <sub>C</sub>                     | collector current             |   |     | -   | -   | -100 | mA   |
| h <sub>FE</sub>                    | DC current gain               | $V_{CE}$ = -5 V; I <sub>C</sub> = -2 mA; T <sub>amb</sub> = 25 °C |     | 200 | 290 | 450  |      |
| Per device                         |                               |   | ·   | ·   |     |      |      |
| h <sub>FE1</sub> /h <sub>FE2</sub> | DC current gain matching      | $V_{CE}$ = -5 V; I <sub>C</sub> = -2 mA; T <sub>amb</sub> = 25 °C | [1] | 0.9 | 1   | -    |      |
| V <sub>BE1</sub> -V <sub>BE2</sub> | base-emitter voltage matching |   | [2] | -   | -   | 2    | mV   |

[1] The smaller of the two values is taken as the numerator.

[2] The smaller of the two values is subtracted from the larger value.

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## 5. Pinning information

| Table 2 | . Pinning info | ormation      |                    |  |
|---------|----------------|---------------|--------------------|--|
| Pin     | Symbol         | Description   | Simplified outline | Graphic symbol                                     |
| 1       | E1             | emitter TR1   |                    | C1 B2 E2   |
| 2       | B1             | base TR1      |                    |  |
| 3       | C2             | collector TR2 |                    | $\left(\begin{array}{c} \\ TR1 \end{array}\right)$ |
| 4       | E2             | emitter TR2   |                    |  |
| 5       | B2             | base TR2      | TSOP6 (SOT457)     | E1 B1 C2   |
| 6       | C1             | collector TR1 |                    | sym018   |

## 6. Ordering information

#### Table 3. Ordering information

| Type number |       |   |               |
|-------------|-------|---|---------------|
|             | Name  | Description   | Version       |
| BCM857DS    | TSOP6 | plastic, surface-mounted package (SC-74; TSOP6); 6<br>leads | <u>SOT457</u> |

#### 7. Marking

# Table 4. Marking codes Type number Marking code BCM857DS R8

## 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol           | Parameter                 | Conditions                          |     | Min | Мах  | Unit |
|------------------|---------------------------|-------------------------------------|-----|-----|------|------|
| Per transiste    | or                        | 1                                   |     |     |      |      |
| V <sub>CBO</sub> | collector-base voltage    | open emitter                        |     | -   | -50  | V    |
| V <sub>CEO</sub> | collector-emitter voltage | open base                           |     | -   | -45  | V    |
| V <sub>EBO</sub> | emitter-base voltage      | open collector                      |     | -   | -5   | V    |
| I <sub>C</sub>   | collector current         |                                     |     | -   | -100 | mA   |
| I <sub>CM</sub>  | peak collector current    | t <sub>p</sub> ≤ 1 ms; single pulse |     | -   | -200 | mA   |
| P <sub>tot</sub> | total power dissipation   | T <sub>amb</sub> ≤ 25 °C            | [1] | -   | 250  | mW   |
| Per device       |                           |                                     | ·   |     |      |      |
| P <sub>tot</sub> | total power dissipation   | T <sub>amb</sub> ≤ 25 °C            | [1] | -   | 380  | mW   |
| Tj               | junction temperature      |                                     |     | -   | 150  | °C   |
| T <sub>amb</sub> | ambient temperature       |                                     |     | -65 | 150  | °C   |
| T <sub>stg</sub> | storage temperature       |                                     |     | -65 | 150  | °C   |

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

## 9. Thermal characteristics

| Symbol               | Parameter                                   | Conditions  |     | Min | Тур | Max | Unit |
|----------------------|---|-------------|-----|-----|-----|-----|------|
| Per transisto        | or  |             | I   |     |     |     | _    |
| R <sub>th(j-a)</sub> | thermal resistance from junction to ambient | in free air | [1] | -   | -   | 500 | K/W  |
| Per device           |   |             |     |     |     |     |      |
| R <sub>th(j-a)</sub> | thermal resistance from junction to ambient | in free air | [1] | -   | -   | 328 | K/W  |

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

## **10.** Characteristics

| Symbol                             | Parameter                       | Conditions   |     | Min  | Тур  | Max  | Unit |
|------------------------------------|---------------------------------|--|-----|------|------|------|------|
| Per transist                       | or                              |  |     |      |      |      |      |
| I <sub>CBO</sub>                   | collector-base cut-off          | V <sub>CB</sub> = -30 V; I <sub>E</sub> = 0 A; T <sub>amb</sub> = 25 °C                                      |     | -    | -    | -15  | nA   |
|                                    | current                         | V <sub>CB</sub> = -30 V; I <sub>E</sub> = 0 A; T <sub>j</sub> = 150 °C                                       |     | -    | -    | -5   | μA   |
| I <sub>EBO</sub>                   | emitter-base cut-off current    | V <sub>EB</sub> = -5 V; I <sub>C</sub> = 0 A; T <sub>amb</sub> = 25 °C                                       |     | -    | -    | -100 | nA   |
| h <sub>FE</sub>                    | DC current gain                 | $V_{CE}$ = -5 V; I <sub>C</sub> = -10 µA; T <sub>amb</sub> = 25 °C   |     | -    | 250  | -    |      |
|                                    |                                 | $V_{CE}$ = -5 V; I <sub>C</sub> = -2 mA; T <sub>amb</sub> = 25 °C  |     | 200  | 290  | 450  |      |
| V <sub>CEsat</sub>                 | collector-emitter               | $I_{C}$ = -10 mA; $I_{B}$ = -0.5 mA; $T_{amb}$ = 25 °C   |     | -    | -50  | -200 | mV   |
|                                    | saturation voltage              | I <sub>C</sub> = -100 mA; I <sub>B</sub> = -5 mA; T <sub>amb</sub> = 25 °C                                   |     | -    | -200 | -400 | mV   |
| V <sub>BEsat</sub>                 | base-emitter saturation voltage | $I_{C}$ = -10 mA; $I_{B}$ = -0.5 mA; $T_{amb}$ = 25 °C   | [1] | -    | -760 | -    | mV   |
|                                    |                                 | $I_{C}$ = -100 mA; $I_{B}$ = -5 mA; $T_{amb}$ = 25 °C  | [1] | -    | -920 | -    | mV   |
| V <sub>BE</sub>                    | base-emitter voltage            | $V_{CE}$ = -5 V; I <sub>C</sub> = -2 mA; T <sub>amb</sub> = 25 °C  | [2] | -600 | -650 | -700 | mV   |
|                                    |                                 | $V_{CE}$ = -5 V; I <sub>C</sub> = -10 mA; T <sub>amb</sub> = 25 °C   | [2] | -    | -    | -760 | mV   |
| C <sub>c</sub>                     | collector capacitance           | V <sub>CB</sub> = -10 V; I <sub>E</sub> = 0 A; i <sub>e</sub> = 0 A;<br>f = 1 MHz; T <sub>amb</sub> = 25 °C  |     | -    | -    | 2.2  | pF   |
| C <sub>e</sub>                     | emitter capacitance             | V <sub>EB</sub> = -0.5 V; I <sub>C</sub> = 0 A; i <sub>c</sub> = 0 A;<br>f = 1 MHz; T <sub>amb</sub> = 25 °C |     | -    | 10   | -    | pF   |
| f <sub>T</sub>                     | transition frequency            | $V_{CE}$ = -5 V; I <sub>C</sub> = -10 mA; f = 100 MHz;<br>T <sub>amb</sub> = 25 °C                           |     | 100  | 175  | -    | MHz  |
| NF                                 | noise figure                    | $V_{CE}$ = -5 V; I <sub>C</sub> = -0.2 mA; R <sub>S</sub> = 2 kΩ; f = 10 kHz to 15.7 kHz                     |     | -    | 1.6  | -    | dB   |
|                                    |                                 | V <sub>CE</sub> = -5 V; I <sub>C</sub> = -0.2 mA; f = 1 kHz;<br>B = 200 Hz                                   |     | -    | 3.1  | -    | dB   |
| Per device                         |                                 | 1  |     | 1    |      |      |      |
| h <sub>FE1</sub> /h <sub>FE2</sub> | DC current gain matching        | $V_{CE}$ = -5 V; I <sub>C</sub> = -2 mA; T <sub>amb</sub> = 25 °C  | [3] | 0.9  | 1    | -    |      |
| V <sub>BE1</sub> -V <sub>BE2</sub> | base-emitter voltage matching   | -  | [4] | -    | -    | 2    | mV   |

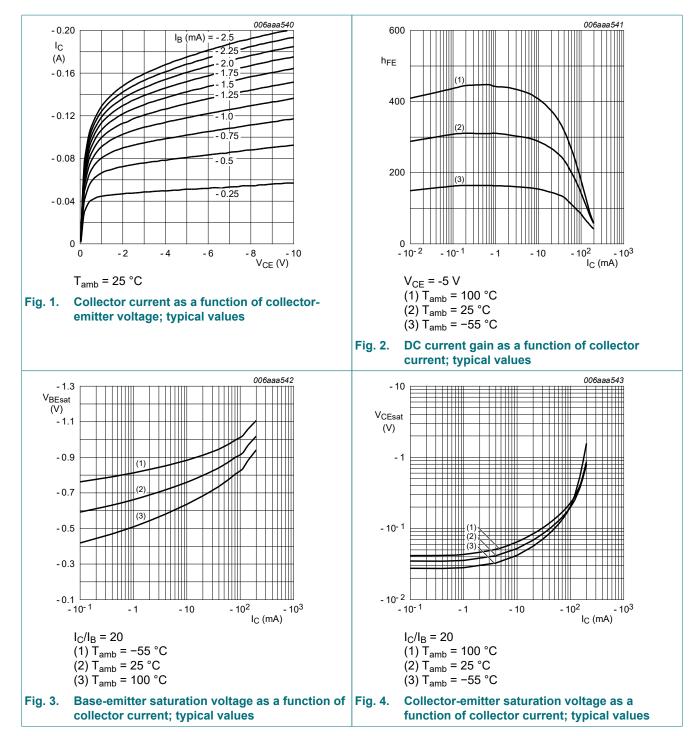
 $V_{BEsat}$  decreases by about 1.7 mV/K with increasing temperature.  $V_{BE}$  decreases by about 2 mV/K with increasing temperature. [1]

[2]

The smaller of the two values is taken as the numerator. [3]

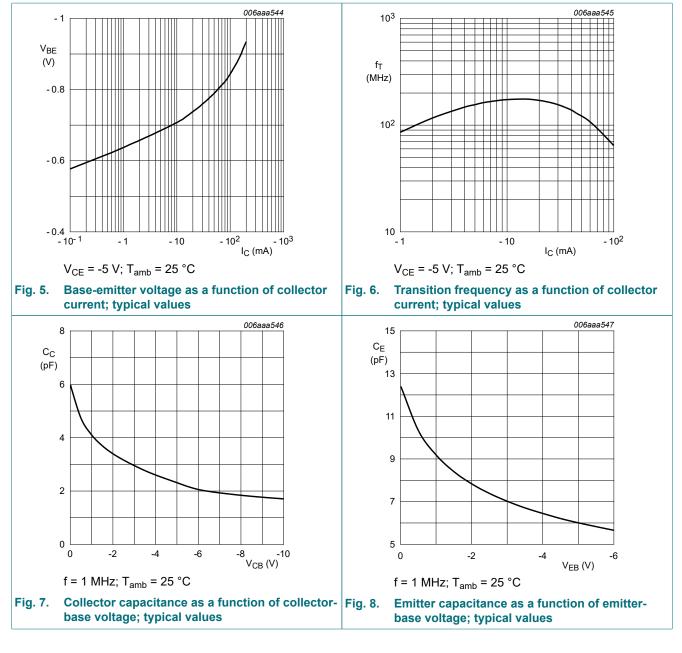
[4] The smaller of the two values is subtracted from the larger value.

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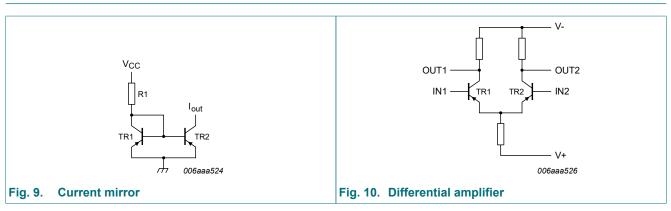


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## **11. Application information**



BCM857DS

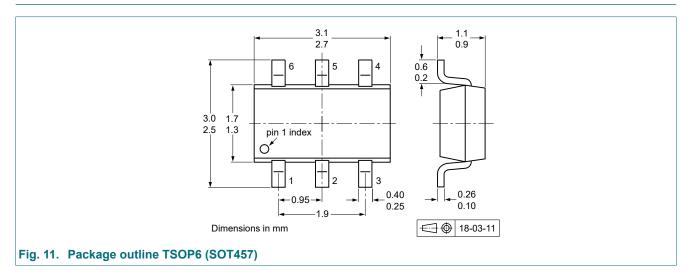
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## **12. Test information**

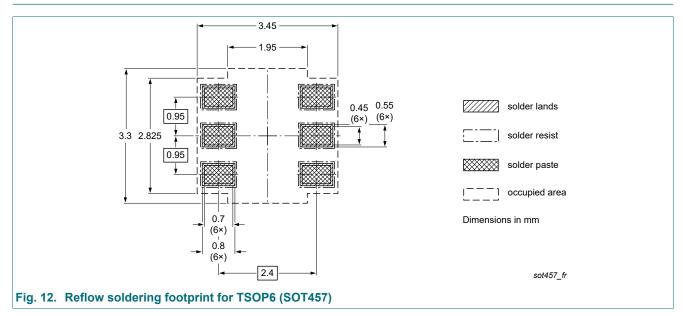
#### **Quality information**

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101* - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

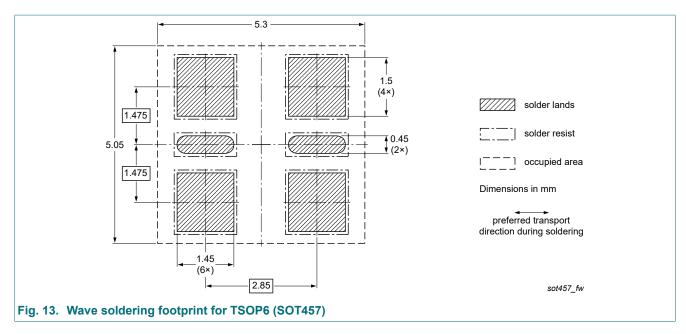
#### 13. Package outline



#### 14. Soldering



#### **PNP/PNP** matched double transistor



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## **15. Revision history**

| Table 8. Revision histo | ry  |                    |               |                  |  |
|-------------------------|---|--------------------|---------------|------------------|--|
| Data sheet ID           | Release date  | Data sheet status  | Change notice | Supersedes       |  |
| BCM857DS v.7            | 20230705  | Product data sheet | -             | BCM857BV_BS_DS_6 |  |
| Modifications:          | <ul> <li>The format of this data sheet has been redesigned to comply with the identity guideling Nexperia.</li> <li>Legal texts have been adapted to the new company name where appropriate.</li> <li>Family data sheet splitted to single type data sheets.</li> <li>Section "Packing information" removed.</li> </ul> |                    |               |                  |  |
| BCM857BV_BS_DS_6        | 20090828  |                    |               | BCM857BV_BS_DS_5 |  |
| BCM857BV_BS_DS_5        | 20060627  | Product data sheet | -             | BCM857BS_DS_4    |  |
| BCM857BS_DS_4           | 20060216  | Product data sheet | -             | BCM857BS_DS_3    |  |
| BCM857BS_DS_3           | 20060130  | Product data sheet | -             | BCM857BS_2       |  |
| BCM857BS_2              | 20050411  | Product data sheet | -             | BCM857BS_1       |  |
| BCM857BS_1              | 20040914  | Product data sheet | -             | -                |  |

## 16. Legal information

#### **Data sheet status**

| Document status [1][2]            | Product<br>status [3] | Definition  |
|-----------------------------------|-----------------------|---|
| Objective [short]<br>data sheet   | Development           | This document contains data from<br>the objective specification for<br>product development. |
| Preliminary [short]<br>data sheet | Qualification         | This document contains data from the preliminary specification.                             |
| Product [short]<br>data sheet     | Production            | This document contains the product specification.   |

 Please consult the most recently issued document before initiating or completing a design.

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